

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC5108FT

For VCO Application

Unit: mm

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	10	V
Emitter-base voltage	V_{EBO}	3	V
Base current	I_B	15	mA
Collector current	I_C	30	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C

		1. BASE 2. EMITTER 3. COLLECTOR
JEDEC	—	
JEITA	—	
TOSHIBA	2-1B1A	

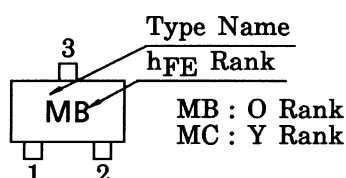
Electrical Characteristics (Ta = 25°C)

Weight: 0.0022 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 10\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	0.1	μA
DC current gain	h_{FE} (Note 1)	$V_{CE} = 5\text{ V}, I_C = 5\text{ mA}$	80	—	240	
Transition frequency	f_T	$V_{CE} = 5\text{ V}, I_C = 5\text{ mA}$	4	6	—	GHz
Insertion gain	$ S_{21e} ^2$	$V_{CE} = 5\text{ V}, I_C = 5\text{ mA}, f = 1\text{ GHz}$	7	11	—	dB
Output capacitance	C_{ob}	$V_{CB} = 5\text{ V}, I_E = 0, f = 1\text{ MHz}$ (Note 2)	—	0.7	—	pF
Reverse transfer capacitance	C_{re}		—	0.5	0.9	pF
Collector-base time constant	$C_C \cdot r_{bb'}$	$V_{CB} = 5\text{ V}, I_C = 3\text{ mA}, f = 30\text{ MHz}$	—	5.5	10	ps

Note 1: h_{FE} classification O: 80~160, Y: 120~240Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Marking



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